What is claimed is:

1. A structure comprising: a first substrate comprising at least one MEMS structure; wherein the first substrate comprises an upper portion and a lower portion, and wherein the at least one MEMS structure includes at least one fixed element that is bonded to the lower portion of the first substrate and at least one moveable element; a first bonding layer disposed directly on the upper portion of the first substrate; at least one pillar structure that is in contact with at least one fixed element, and wherein the at least one pillar structure is disposed between the upper portion of the first substrate and a lower portion of the first substrate, wherein the at least one pillar structure and the upper portion of the first substrate comprise an hermetic seal for the at least one MEMS structure; and a second bonding layer disposed on a surface of a second substrate, wherein the second bonding layer is disposed on a device layer of the second substrate, and wherein the first bonding layer is directly bonded to the second bonding layer.

2. The structure of claim 1 further comprising wherein the first bonding layer comprises one of a metal layer or an oxide layer.

3. The structure of claim 1 further comprising wherein the at least one MEMS structure comprises at least one of a resonator, an actuator, a gyroscope, a sensor, an accelerometer, and a compass.

4. The structure of claim 1 further comprising wherein the first substrate comprises a single crystal silicon substrate.

5. The structure of claim 1 further comprising wherein the upper portion of the first substrate and the pillar structure comprise an epitaxial material.

6. The structure of claim 1 further comprising wherein the second substrate comprises at least one microelectronic die.

7. The structure of claim 1 further comprising wherein the bond between the first bonding layer and the second bonding layer comprises one of a metal to metal bond or an oxide to oxide bond.

8. The structure of claim 1 further comprising wherein the second substrate comprises one of a high voltage IC and an RF IC.

9. The structure of claim 1 further comprising wherein the first substrate comprises a silicon on insulator substrate.

10. The structure of claim 1 further comprising wherein at least one of the MEMS structures are coupled to the device layer by conductive contacts disposed between portions of individual device structures within the device layer and the MEMS structures.

11. The structure of claim 1 wherein the second substrate further comprises at least one of a CPU and a memory die.

12. The structure of claim 1 wherein the second substrate further comprises a portion of a system on a chip.

13. The structure of claim 1 further comprising a system comprising: a bus communicatively coupled to the structure; and an eDRAM communicatively coupled to the bus.

14. The structure of claim 1, wherein the first bonding layer comprises a dielectric material, and does not comprise a conductive element.